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# DMP6110SVTQ-7

**Diodes Incorporated** 

**MOSFET MOSFET BVDSS: 41V-60V** 

Any questions, please feel free to contact us. info@kaimte.com





### **P-CHANNEL ENHANCEMENT MODE MOSFET**

### **Product Summary**

BV <sub>DSS</sub>	R <sub>DS(ON)</sub> Max	I <sub>D</sub> Max T <sub>C</sub> = +25°C
	105mΩ @ V <sub>GS</sub> = -10V	-7.3A
-60V	130mΩ @ V <sub>GS</sub> = -4.5V	-6.5A

### **Features and Benefits**

- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

### **Description and Applications**

This MOSFET is designed to meet the stringent requirements of automotive applications. It is qualified to AEC-Q101, supported by a PPAP and is ideal for use in:

- Backlighting
- Power Management Functions
- DC-DC Converters

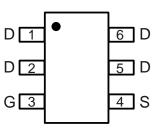
### **Mechanical Data**

- Case: TSOT26
- Case Material: Molded Plastic, "Green" Molding Compound.
   UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See Diagram
- Terminals: Finish Matte Tin Annealed over Copper Leadframe.
   Solderable per MIL-STD-202, Method 208 <sup>3</sup>
- Weight: 0.008 grams (Approximate)

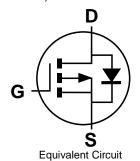








**Device Schematic** 



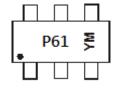
### **Ordering Information** (Note 5)

Case	Packaging
TSOT26	3,000/Tape & Reel
TSOT26	10,000/Tape & Reel
	TSOT26

Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.

- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. Automotive products are AEC-Q101 qualified and are PPAP capable. Refer to https://www.diodes.com/quality/.
- 5. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

### Marking Information



P61 = Product Type Marking Code YM or \( \overline{YM} = Date Code Marking Y = Year (ex: F = 2018) M = Month (ex: 9 = September)

Date Code Key

Date Code Key									
Year	2016	2017	2018	2019	2020	2021	2022	2023	2024
Code	D	Е	F	G	Н	I	J	K	L

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



### **Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Drain-Source Voltage		V <sub>DSS</sub>	-60	V
Gate-Source Voltage		V <sub>GSS</sub>	±20	V
Continuous Drain Current (Note 7) V <sub>GS</sub> = -10V	I <sub>D</sub>	-7.3 -5.8	А	
Maximum Body Diode Forward Current (Note 7)		Is	-1.8	Α
Pulsed Drain Current (380µs Pulse, 1% Duty Cycle)	I <sub>DM</sub>	-24	Α	
Pulsed Source Current (380µs Pulse, 1% Duty Cycle)	I <sub>SM</sub>	-24	Α	
Avalanche Current (Note 7) L = 0.1mH	I <sub>AS</sub>	-19	А	
Repetitive Avalanche Energy (Note 7) L = 0.1mH		E <sub>AS</sub>	18	mJ

### Thermal Characteristics ( $@T_A = +25^{\circ}C$ , unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Total Power Dissipation (Note 6)	T <sub>A</sub> = +25°C	Б	1.2	W
Total Power Dissipation (Note 6)	T <sub>A</sub> = +70°C	P <sub>D</sub>	0.75	VV
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	D	105	°C/W
Thermal Resistance, Junction to Ambient (Note 6)	t<10s	$R_{\theta JA}$	60	°C/W
Total Power Dissipation (Note 7)	$T_A = +25^{\circ}C$	P <sub>D</sub>	1.8	W
Total Fower Dissipation (Note 1)	T <sub>A</sub> = +70°C	FD	1.1	VV
Thermal Resistance, Junction to Ambient (Note 7)	Steady State	D	69	°C/W
Thermal Resistance, Junction to Ambient (Note 1)	t<10s	R <sub>0JA</sub>	39	°C/W
Thermal Resistance, Junction to Case (Note 7)	$R_{ heta JC}$	15	°C/W	
Operating and Storage Temperature Range		T <sub>J,</sub> T <sub>STG</sub>	-55 to +150	°C

### **Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition		
OFF CHARACTERISTICS (Note 8)								
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	-60	_	_	V	$V_{GS} = 0V, I_{D} = -250\mu A$		
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	_	_	-1	μΑ	$V_{DS} = -48V, V_{GS} = 0V$		
Gate-Source Leakage	I <sub>GSS</sub>	_	_	-100	nA	$V_{GS} = \pm 16V, V_{DS} = 0V$		
ON CHARACTERISTICS (Note 8)			•	•	•			
Gate Threshold Voltage	V <sub>GS(TH)</sub>	-1	_	-3	V	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$		
Static Drain-Source On-Resistance		_	_	105	mΩ	$V_{GS} = -10V, I_{D} = -4.5A$		
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	_	_	130	111122	$V_{GS} = -4.5V, I_D = -3.5A$		
Diode Forward Voltage	V <sub>SD</sub>	_	-0.7	-1.2	V	$V_{GS} = 0V, I_{S} = -1A$		
DYNAMIC CHARACTERISTICS (Note 9)								
Input Capacitance	C <sub>ISS</sub>	_	969	_		V <sub>DS</sub> = -30V, V <sub>GS</sub> = 0V, f = 1.0MHz		
Output Capacitance	Coss	_	57	_	pF			
Reverse Transfer Capacitance	C <sub>RSS</sub>	_	44	_				
Gate Resistance	R <sub>G</sub>		13.7	_	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1.0MHz$		
Total Gate Charge (V <sub>GS</sub> = -4.5V)	$Q_{G}$	_	8.2	_				
Total Gate Charge (V <sub>GS</sub> = -10V)	$Q_{G}$	_	17.2	_		V 00V I 40A		
Gate-Source Charge	Q <sub>GS</sub>	_	3.0	_	nC	$V_{DS} = -30V, I_{D} = -12A$		
Gate-Drain Charge	$Q_GD$	_	3.1	_				
Turn-On Delay Time	t <sub>D(ON)</sub>	_	4.4	_				
Turn-On Rise Time	t <sub>R</sub>	_	23	_		$V_{GS} = -10V$ , $V_{DS} = -30V$ , $R_{GEN} = 3\Omega$ ,		
Turn-Off Delay Time	t <sub>D(OFF)</sub>	_	34	_	ns	I <sub>D</sub> = -12A		
Turn-Off Fall Time	t <sub>F</sub>	_	42	_				
Body Diode Reverse Recovery Time	t <sub>RR</sub>	_	13.2	_	ns	100 11/11 1000/		
Body Diode Reverse Recovery Charge	Q <sub>RR</sub>	_	6.18	_	$I_{S} = -12A$ , $dI/dt = 100A/\mu s$			

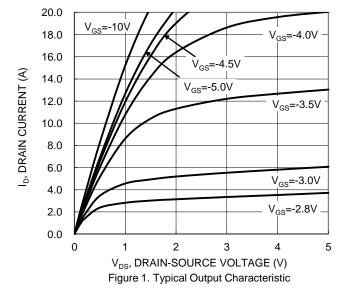
Notes: 6. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.

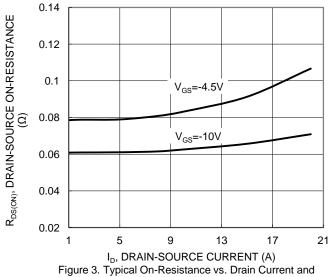
7. Device mounted on FR-4 substrate PC board, 2oz copper, with 1-inch square copper plate.

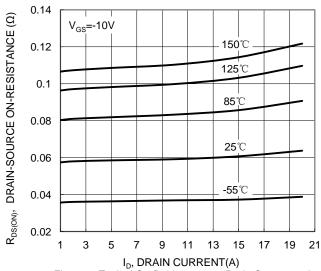
8. Short duration pulse test used to minimize self-heating effect.

9. Guaranteed by design. Not subject to product testing.



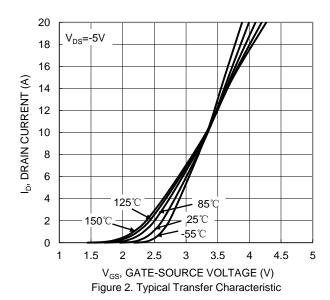






Gate Voltage

Figure 5. Typical On-Resistance vs. Drain Current and Temperature



0.3 R<sub>DS(ON)</sub>, DRAIN-SOURCE ON-RESISTANCE 0.25 0.2  $I_{D} = -4.5A$ 0.15 0.1 0.05  $I_{D} = -3.5A$ 0 0 8 12 16 20  $V_{GS}$ , GATE-SOURCE VOLTAGE (V)

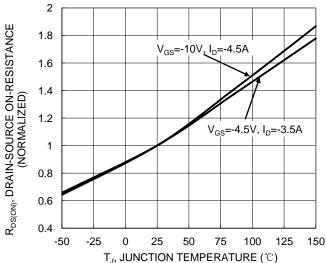


Figure 4. Typical Transfer Characteristic

Figure 6. On-Resistance Variation with Temperature



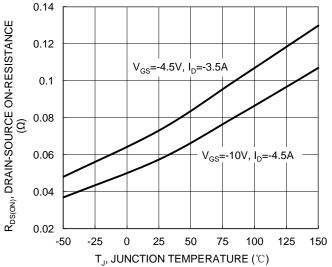
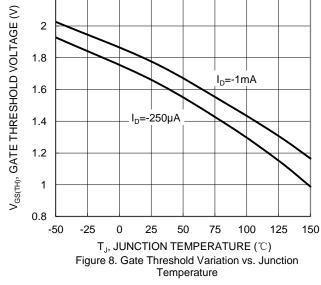


Figure 7. On-Resistance Variation with Temperature



2.2

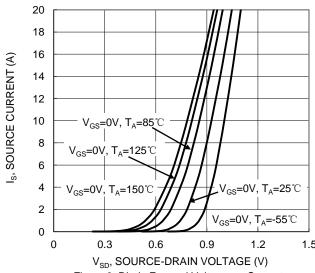
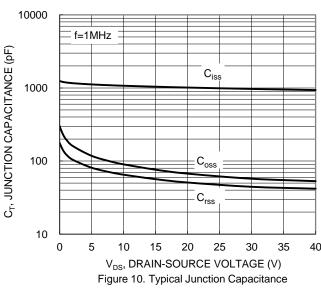
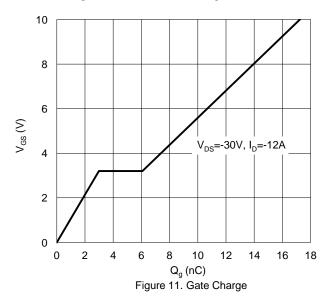
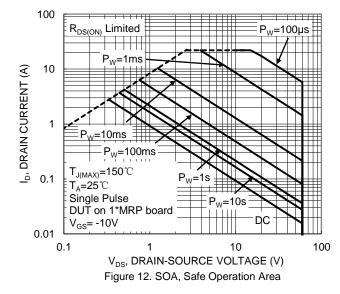


Figure 9. Diode Forward Voltage vs. Current









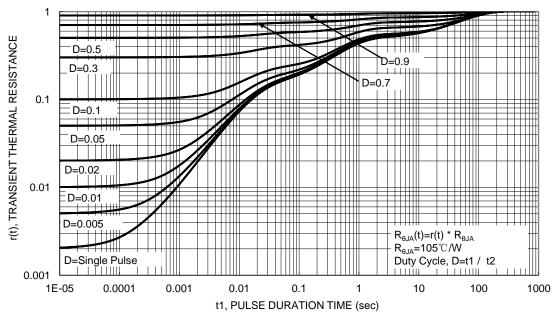


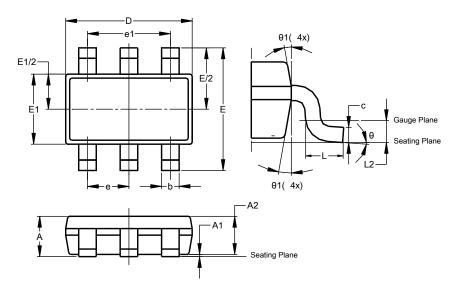
Figure 13. Transient Thermal Resistance



### **Package Outline Dimensions**

 $Please see \ http://www.diodes.com/package-outlines.html \ for \ the \ latest \ version.$ 

### TSOT26

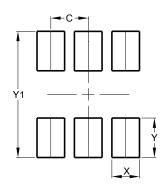


TSOT26							
Dim	Min	Max	Тур				
Α	-	1.00	-				
A1	0.010	0.100	-				
A2	0.840	0.900	-				
D	2.800	3.000	2.900				
Е	2.800 BSC						
E1	1.500	1.700	1.600				
b	0.300	0.450	-				
С	0.120	0.200	-				
е	C	.950 BS	С				
e1	1	.900 BS	С				
Г	0.30	0.50	-				
L2	0.250 BSC						
θ	0°	8°	4°				
θ1	4°	12°	-				
All Dimensions in mm							

### **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.

### TSOT26



Dimensions	Value (in mm)
C	0.950
Х	0.700
Y	1.000
Y1	3.199



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